CD4086B Types

CMOS Expandable 4-Wide 2-Input AND-OR-INVERT Gate

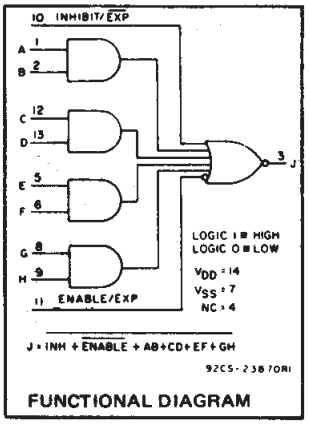
High-Voltage Types (20-Volt Rating)

■ CD4086B contains one 4-wide 2-input AND-OR-INVERT gate with an INHIBIT/$\overline{EXP}$ input and an ENABLE/EXP input. For a 4-wide A-O-I function INHIBIT/$\overline{EXP}$ is tied to V_{SS} and ENABLE/EXP to V_{DD}. See Fig.10 and its associated explanation for applications where a capability greater than 4-wide is required.

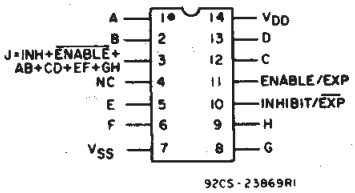
The CD4086B is supplied in 14-lead dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

- Medium-speed operation – t_{PHL} = 90 ns; t_{PLH} = 140 ns (typ.) at 10 V
- INHIBIT and ENABLE inputs
- Buffered outputs
- 100% tested for quiescent current at 20 V
- Maximum input leakage current of 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package termperature range):
  1 V at V_{DD} = 5 V
  2 V at V_{DD} = 10 V
  2.5 V at V_{DD} = 15 V
- Standardized, symmetrical output characteristics
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"



FUNCTIONAL DIAGRAM



Top View

TERMINAL ASSIGNMENT

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
Voltages referenced to V_{SS} Terminal) ..... -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C ..... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mW
OPERATING-TEMPERATURE RANGE (T_A) ..... -55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

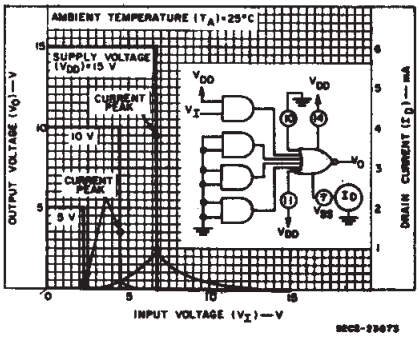


Fig. 1 – Typical voltage and current transfer characteristics.

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A = Full Package-Temperature Range)	3	18	V

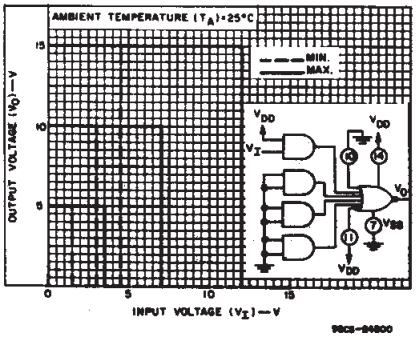


Fig. 2 – Minimum and maximum voltage transfer characteristics.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	+25 Min.	+25 Typ.	+25 Max.	
Quiescent Device Current I_{DD} Max.	–	0,5	5	1	1	30	30	–	0.02	1	μA
	–	0,10	10	2	2	60	60	–	0.02	2	
	–	0,15	15	4	4	120	120	–	0.02	4	
	–	0,20	20	20	20	600	600	–	0.04	20	
Output Low (Sink) Current, I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	0.5,4.5	–	5	1.5				–	–	1.5	V
	1,9	–	10	3				–	–	3	
	1.5,13.5	–	15	4				–	–	4	
Input High Voltage, V_{IH} Min.	0.5,4.5	–	5	3.5				3.5	–	–	
	1,9	–	10	7				7	–	–	
	1.5,13.5	–	15	11				11	–	–	
Input Current, I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

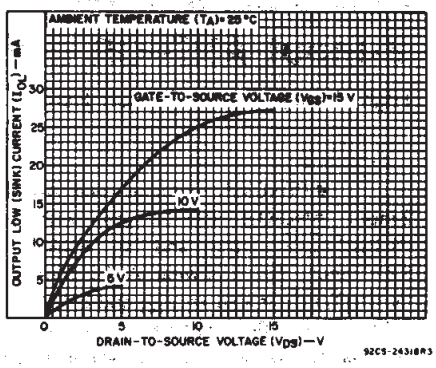


Fig. 3 – Typical output low (sink) current characteristics.

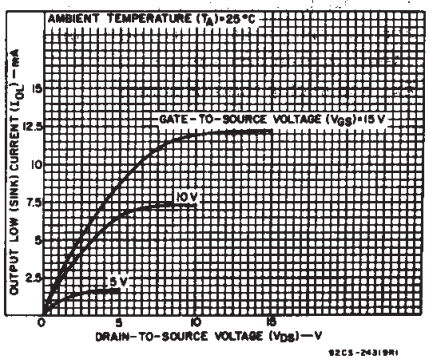


Fig. 4 – Minimum output low (sink) current characteristics.

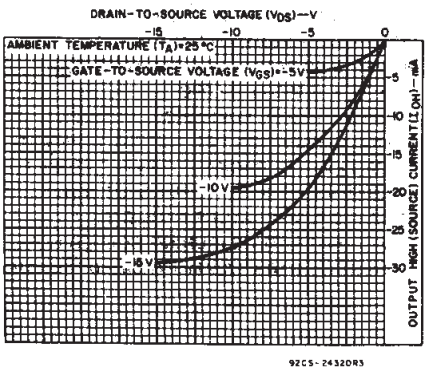


Fig.5 – Typical output high (source) current characteristics.

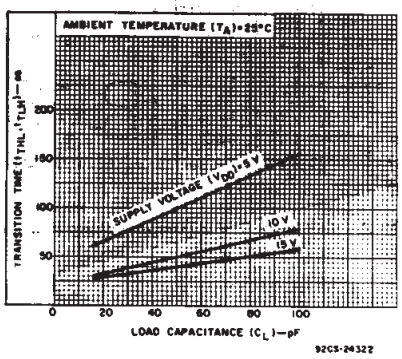


Fig.6 – Typical transition time vs. load capacitance.

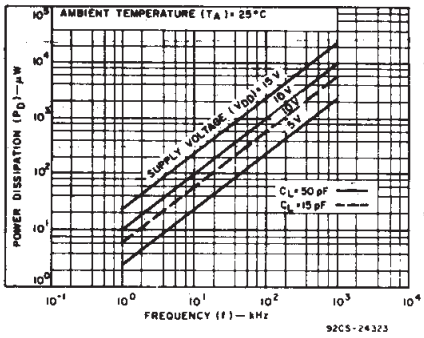


Fig.7 – Typical power dissipation vs. frequency.

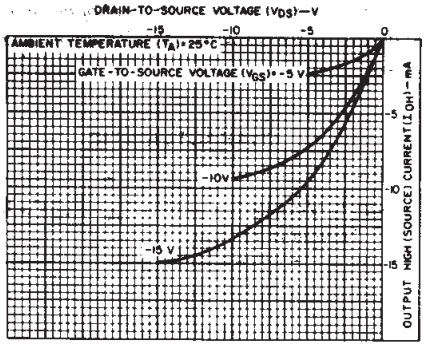


Fig.8 – Minimum output high (source) current characteristics.

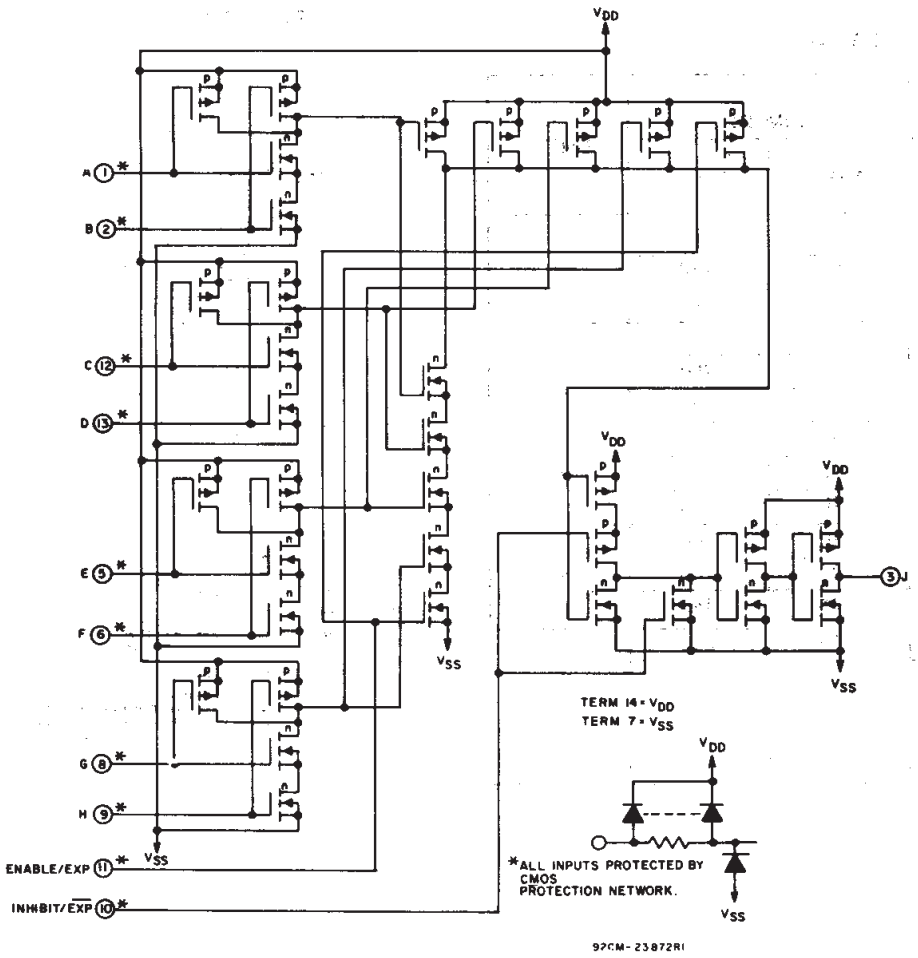


Fig. 9 – CD4086B schematic diagram.

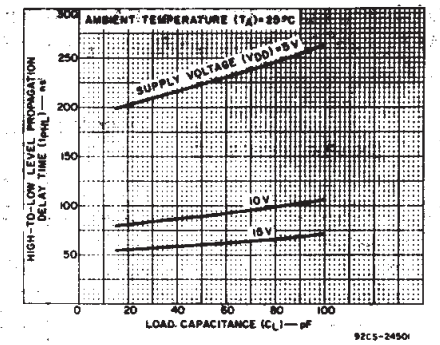


Fig. 11 – Typical DATA or ENABLE high-to-low level propagation delay time vs. load capacitance.

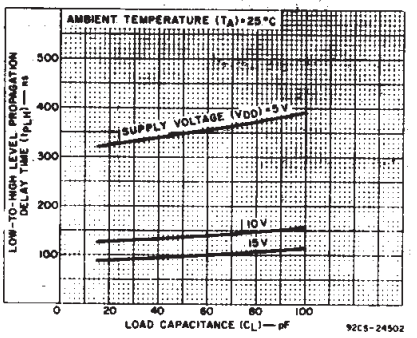


Fig. 12 – Typical DATA or ENABLE low-to-high level propagation delay time vs. load capacitance.

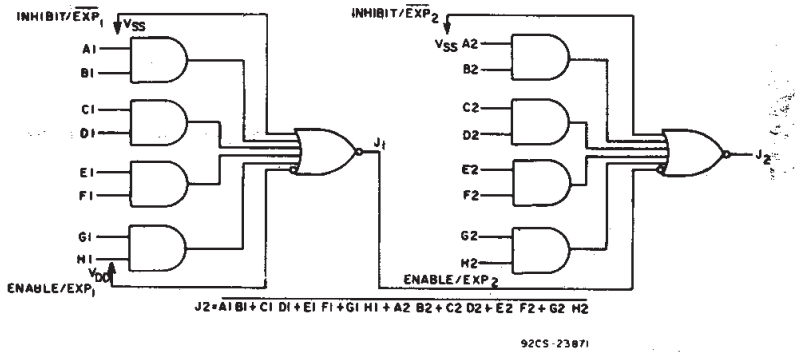


Fig. 10 – Two CD4086B's connected as an 8-wide 2-input A-O-I gate.

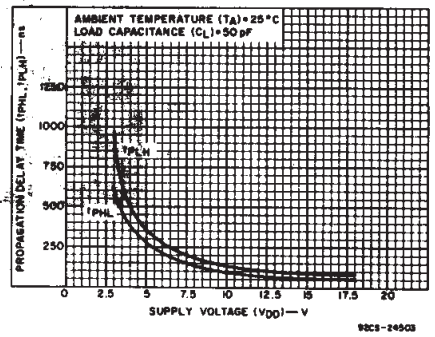


Fig. 13 – Typical DATA or ENABLE propagation delay time vs. supply voltage.

Fig. 10 above shows two CD4086's utilized to obtain an 8-wide 2-input A-O-I function. The output (J1) of one CD4086 is fed directly to the ENABLE/EXP2 line of the second CD4086. In a similar fashion, any NAND gate output can be fed directly into the ENABLE/EXP input to obtain a 5-wide A-O-I function. In addition, any AND gate output can be fed directly into the INHIBIT/$\overline{\text{EXP}}$ input with the same result.

DYNAMIC ELECTRICAL CHARACTERISTICS

At T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 kΩ

CHARACTERISTIC	CONDITIONS	LIMITS		UNITS
	V_{DD} (V)	TYP.	MAX.	
Propagation Delay Time (Data): High-to-Low Level, t_{PHL}	5	225	450	ns
	10	90	180	
	15	60	120	
Low-to-High Level, t_{PLH}	5	310	620	ns
	10	125	250	
	15	90	180	
Propagation Delay Time (Inhibit): High-to-Low Level, $t_{PHL(INH)}$	5	150	300	ns
	10	60	120	
	15	40	80	
Low-to-High Level, $t_{PLH(INH)}$	5	250	500	ns
	10	100	200	
	15	70	140	
Transition Time, t_{THL}, t_{TLH}	5	100	200	ns
	10	50	100	
	15	40	80	
Input Capacitance C_{IN}	Any Input	5	7.5	pF

TEST CIRCUITS

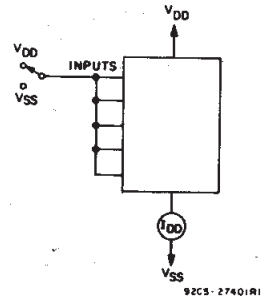


Fig. 14 – Quiescent device current.

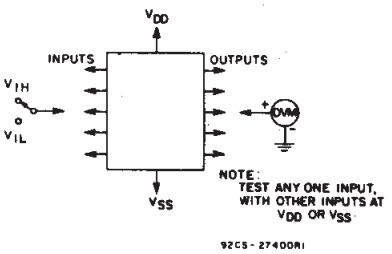


Fig. 15 – Input voltage.

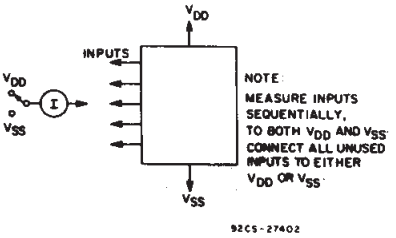
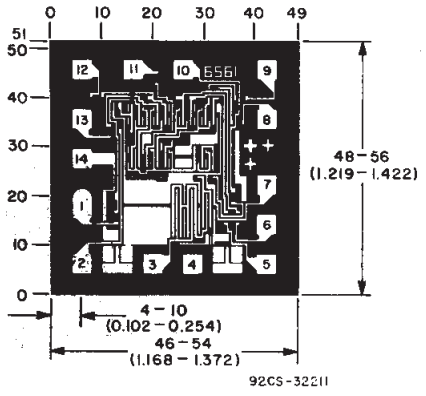


Fig. 16 – Input leakage current.



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

Dimensions and Pad Layout for the CD4086BH

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